

# FUKUCOM COMPANY LTD.

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### RECTIFIER SPECIALISTS

1N60P

# TECHNICAL SPECIFICATIONS OF SMALL SIGNAL SCHOTTKY DIODES

#### **FEATURES**

- \* Metal silicon junction, majority carrier conduction.
- \* High current capability, low forward voltage drop.
- \* Extremely low reverse current IR
- \* Ultra speed switching characteristics
- \* Small temperature coefficient of forward characteristics
- \* Satisfactory Wave detection efficiency
- \* For use in RECORDER, TV, RADIO, TELEPHONE as detectors, super high speed switching circuits, small current rectifier

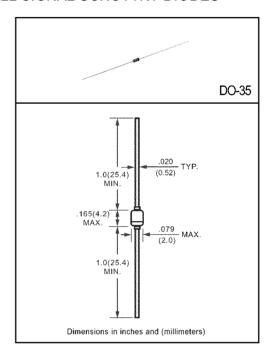
#### MECHANICAL DATA

- \* Case: DO-35 glass case
- \* Polarity: color band denotes cathode end
- \* Weight: 0.13 grams approx.

#### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified. Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate current by 20%.

ABSOLUTE RATINGS(LIMITING VALUES)



PARAMETERS		SYMBOL	VALUE	UNITS
ZeneRepetitive Peak Reverse Voltage		VRRM	45	Volts
Forward Continuous Current	T <sub>A</sub> =25°C	lF	50	mA
Peak Forward Surge Current(t=1S)		Irsm	500	mA
Storage and junction Temperature Range		Tstg/TJ	-65 to +125	°c
Maximum Lead Temperature for Soldering during 10S at 4mm from Case		TL	230	°c

# **ELECTRICAL CHARACTERISTICS**

DADANETED C	TEST CONDITIONS	SYMBOL	VALUE		
PARAMETERS	TEST CONDITIONS		TYP.	MAX.	UNITS
Forward Voltage	l∈=1mA	VF	0.24	0.5	Volts
	⊫=200mA		0.65	1.0	
Reverse Current	V <sub>R</sub> =15V	lR	0.5	1.0	μΑ
Junction Capacitance	V <sub>R</sub> =10V f=1MHz	C∪	6.0		pF
Detection Efficiency	V <sub>I</sub> =3V f=30MHz C <sub>L</sub> =10pF R <sub>L</sub> =3.8KΩ	η	60		%
Reverse Recovey time	F= R=1mA   Irr=1mA   Rc=100Ω	trr		1	ns
Junction Ambient Thermal Resistance		ReJA	400		°C/W